

**MMBT3906** TRANSISTOR (PNP)

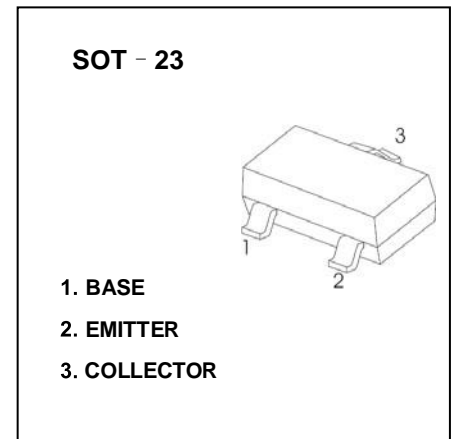
**FEATURES**

- As complementary type, the NPN transistor MMBT3904 is Recommended
- Epitaxial planar die construction

**MARKING: 2A**

**MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Units
V <sub>CB0</sub>	Collector-Base Voltage	-50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-40	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>c</sub>	Collector Current -Continuous	-0.2	A
P <sub>C</sub>	Collector Dissipation	0.2	W
R <sub>θJA</sub>	Thermal resistance junction to ambient	625	°C/W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C



**ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>c</sub> = -100uA	-50		V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>c</sub> = -1mA, I <sub>B</sub> = 0	-40		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -100uA	-5		V
Collector cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = -40 V, I <sub>E</sub> = 0		-100	nA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> = -35V		-1.0	uA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> = 0		-100	nA
DC current gain	h <sub>FE1</sub>	V <sub>CE</sub> = -1V, I <sub>c</sub> = -10mA	100	400	
	h <sub>FE2</sub>	V <sub>CE</sub> = -1V, I <sub>c</sub> = -50mA	60		
	h <sub>FE3</sub>	V <sub>CE</sub> = -1V, I <sub>c</sub> = -100mA	30		
Collector-emitter saturation voltage	V <sub>CE(sat)1</sub>	I <sub>c</sub> = -50mA, I <sub>B</sub> = -5mA		-0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>c</sub> = -50mA, I <sub>B</sub> = -5mA		-1.0	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -20V, I <sub>c</sub> = -10mA, f = 100MHz	300		MHz

**CLASSIFICATION OF h<sub>FE(1)</sub>**

HFE	100-300	
RANK	L	H
RANGE	100 - 200	200 - 300

